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FORM PTO – 1449 INFORMATION DISCLOSURE STATEMENT	ATTORNEY DOCKET NO.: WPG-001 APPLICANT(S): Chang et al. SERIAL NO.: 10/715,743 2829 FILING DATE: 11/17/03 GROUP: Not Yet Assigned

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AKS	A1	6,143,626	11/07/00	Yabu et al.			
	A2	5,918,142	06/29/99	Park et al.			
	A3	5,834,346	11/10/98	Sun et al.			
	A4	5,759,886	06/02/98	Chung			
	A5	5,728,627	03/17/98	Nam et al.			
	A6	5,716,891	02/10/98	Kodama			
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	A8	5,006,480	04/09/91	Chang et al.			
	A9	4,935,380	06/19/90	Okumura			
	A10	4,830,974	05/16/89	Chang et al.			
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AKS	A12	4,363,830	12/14/82	Hsu et al.			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
AKS	C1	*Formation of submicron T-gate by rapid thermally reflowed resist with metal transfer layer*, C.C. Meng, G.R. Liao and S.S. Lu: ELECTRONICS LETTERS, Vol. 37 No. 16 (2001) pp. 1045-1046.
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AKS	C4	*30-nm-Gate InP-Based Lattice-Matched High Electron Mobility Transistors with 350 GHz Cutoff Frequency*, T. Suemitsu, T. Ishii, H. Yokoyama, T. Enoki, Y. Ishii and T. Tamamura: Jpn. J. Appl. Phys. Vol. 38 (1999) pp. L154-156.
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EXAMINER Asok Kumar Sarkar	DATE CONSIDERED 8/16/04